

Title (en)

IMAGE SENSOR FOR IMAGING AT A VERY LOW LEVEL OF LIGHT

Title (de)

BILDSSENSOR FÜR DIE BILDGEBUNG BEI SEHR SCHWACHER BELEUCHTUNG

Title (fr)

CAPTEUR D'IMAGE POUR IMAGERIE A TRES BAS NIVEAU DE LUMIERE

Publication

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Application

EP 10731768 A 20100511

Priority

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Abstract (en)

[origin: WO2010130951A1] The invention relates to a basic device for an image sensor, including a photogeneration and charge-collecting region formed at the surface of a semiconductor substrate having a first type of conductivity (30), adapted to be biased at a reference voltage, the photogeneration region being associated with a device for the transfer (36), multiplication (38, 40, 42) and insulation (44) of charges. The photogeneration region has an insulated gate (32) mounted thereon, which is adapted to be alternately biased at a first voltage and at a second voltage, the insulated gate being made of a low-absorption material.

IPC 8 full level

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CPC (source: EP US)

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